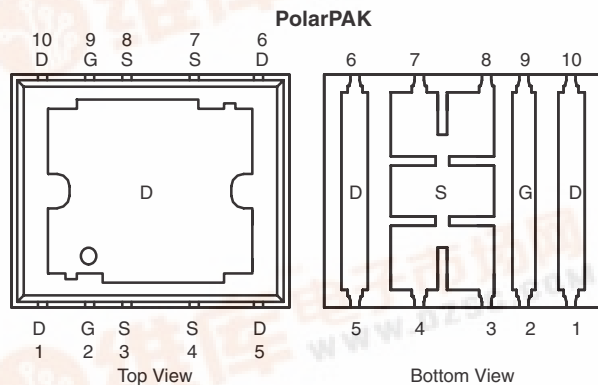


N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) ^e	I _D (A)		Q _g (Typ.)
		Silicon Limit	Package Limit	
30	0.0021 at V _{GS} = 10 V	178	60 ^a	34 nC
	0.0028 at V _{GS} = 4.5 V	154	60 ^a	

Package Drawing

www.vishay.com/doc?68796

Top surface is connected to pins 1, 5, 6, and 10

Ordering Information: SiE860DF-T1-E3 (Lead (Pb)-free)
SiE860DF-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

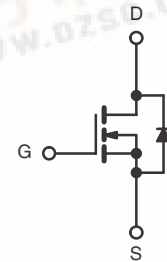
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Gen III Power MOSFET
- Ultra Low Thermal Resistance Using Top-Exposed PolarPAK[®] Package for Double-Sided Cooling
- Leadframe-Based New Encapsulated Package
 - Die Not Exposed
 - Same Layout Regardless of Die Size
- Low Q_{gd}/Q_{gs} Ratio Helps Prevent Shoot-Through
- 100 % R_g and UIS Tested
- Compliant to RoHS directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- VRM, POL
- DC/DC Conversion
- Synchronous Rectification
- Server



N-Channel MOSFET

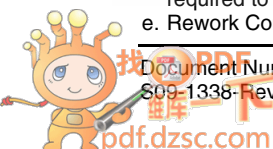
For Related Documents
www.vishay.com/ppg?68786

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	178 (Silicon Limit)
			60 ^a (Package Limit)
		T _C = 70 °C	60 ^a
		T _A = 25 °C	38 ^{b, c}
		T _A = 70 °C	31 ^{b, c}
Pulsed Drain Current	I _{DM}	80	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	60 ^a
		T _A = 25 °C	4.3 ^{b, c}
Single Pulse Avalanche Current	I _{AS}	50	
Avalanche Energy	E _{AS}	125	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	104
		T _C = 70 °C	66
		T _A = 25 °C	5.2 ^{b, c}
		T _A = 70 °C	3.3 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

Notes:

- Package limited at 60 A.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- See Solder Profile (www.vishay.com/ppg?73257). The PolarPAK is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



SiE860DF


[Vishay Siliconix 供应商](#)

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, b}	$t \leq 10$ s	R_{thJA}	20	24	°C/W
Maximum Junction-to-Case (Drain Top)	Steady State	R_{thJC} (Drain)	0.9	1.1	
Maximum Junction-to-Case (Source) ^{a, c}		R_{thJC} (Source)	2.7	3.3	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
 b. Maximum under Steady State conditions is 68 °C/W.
 c. Measured at source pin (on the side of the package).

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted

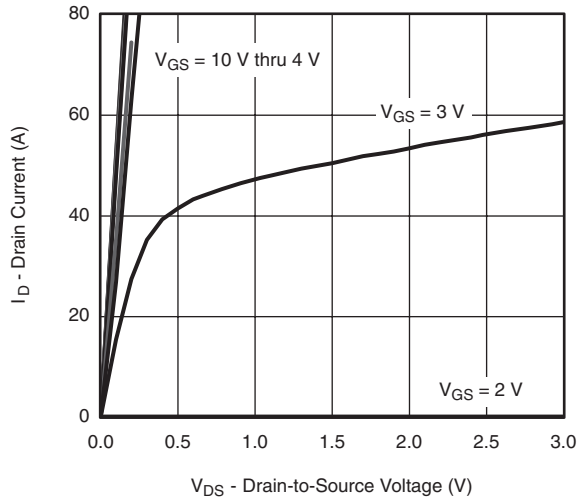
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μ A	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ μ A		30		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		- 6.1			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μ A	1.0		2.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30$ V, $V_{GS} = 0$ V			1	μ A
		$V_{DS} = 30$ V, $V_{GS} = 0$ V, $T_J = 55$ °C			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5$ V, $V_{GS} = 10$ V	25			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 21.7$ A		0.0017	0.0021	Ω
		$V_{GS} = 4.5$ V, $I_D = 19$ A		0.0023	0.0028	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15$ V, $I_D = 21.7$ A		110		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15$ V, $V_{GS} = 0$ V, $f = 1$ MHz		4500		pF
Output Capacitance	C_{oss}		850			
Reverse Transfer Capacitance	C_{rss}		300			
Total Gate Charge	Q_g	$V_{DS} = 15$ V, $V_{GS} = 10$ V, $I_D = 20$ A		70	105	nC
		$V_{DS} = 15$ V, $V_{GS} = 4.5$ V, $I_D = 20$ A		34	51	
Gate-Source Charge	Q_{gs}			14		
Gate-Drain Charge	Q_{gd}		9			
Gate Resistance	R_g	$f = 1$ MHz		0.9	1.8	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15$ V, $R_L = 1.5$ Ω $I_D \cong 10$ A, $V_{GEN} = 4.5$ V, $R_g = 1$ Ω		35	55	ns
Rise Time	t_r		20	30		
Turn-Off Delay Time	$t_{d(off)}$		50	75		
Fall Time	t_f		30	45		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15$ V, $R_L = 1.5$ Ω $I_D \cong 10$ A, $V_{GEN} = 10$ V, $R_g = 1$ Ω		16	25	
Rise Time	t_r		10	15		
Turn-Off Delay Time	$t_{d(off)}$		40	30		
Fall Time	t_f		10	15		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C			60	A
Pulse Diode Forward Current ^a	I_{SM}				80	
Body Diode Voltage	V_{SD}	$I_S = 10$ A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10$ A, $di/dt = 100$ A/ μ s, $T_J = 25$ °C		35	55	ns
Body Diode Reverse Recovery Charge	Q_{rr}			30	45	nC
Reverse Recovery Fall Time	t_a			21		ns
Reverse Recovery Rise Time	t_b			14		

Notes:

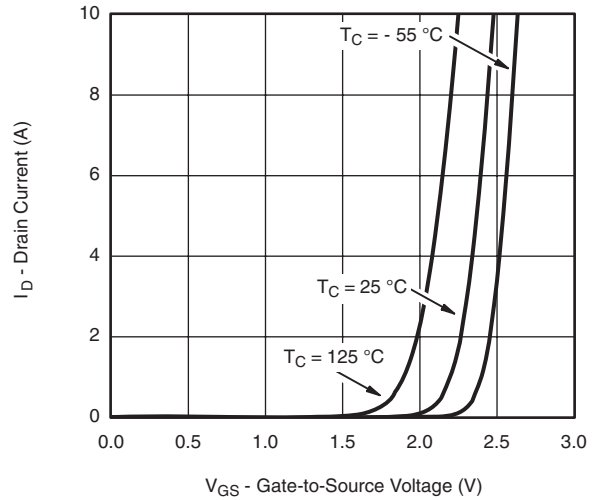
- a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

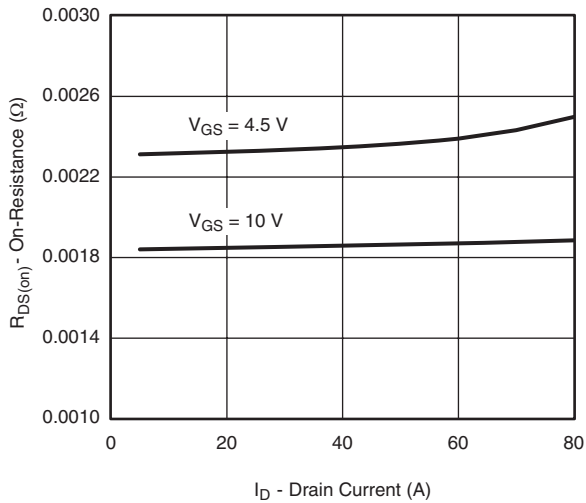
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



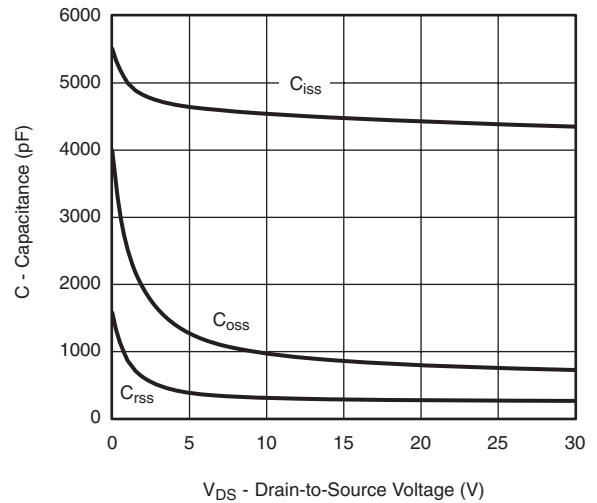
Output Characteristics



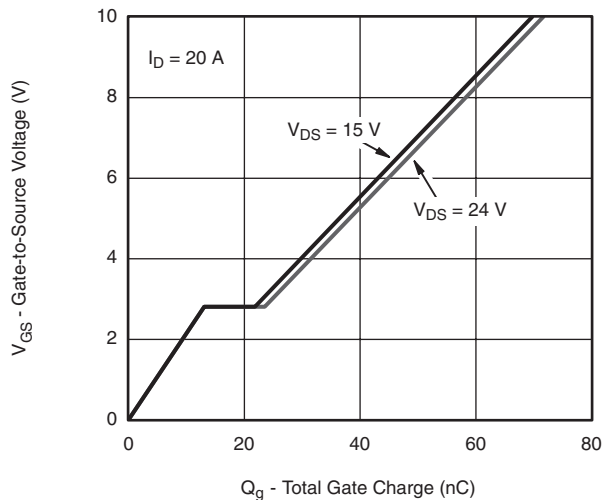
Transfer Characteristics



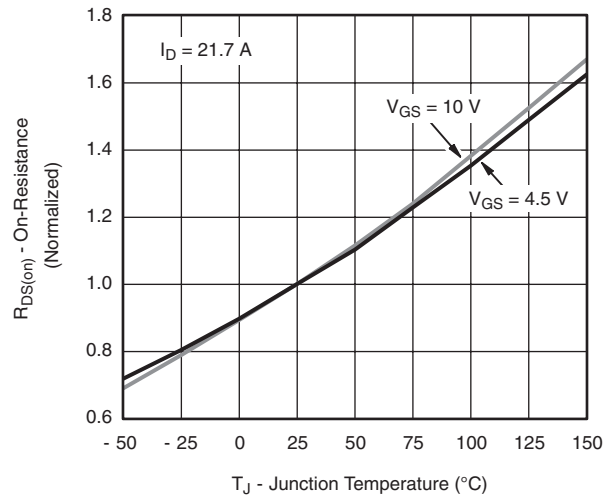
On-Resistance vs. Drain Current



Capacitance



Gate Charge



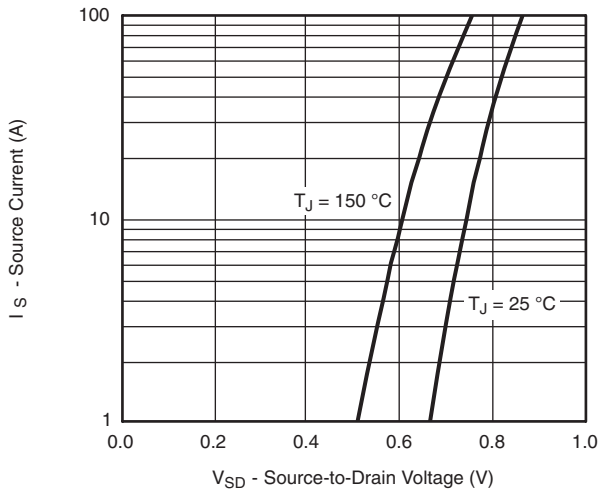
On-Resistance vs. Junction Temperature

SiE860DF

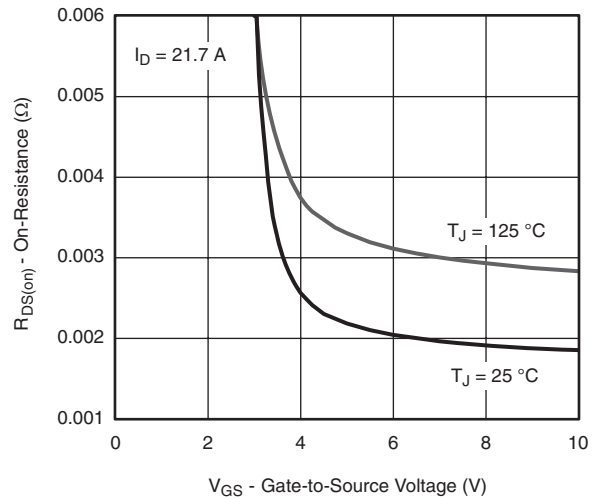


上海“SiE860DF”供应商
Vishay Siliconix

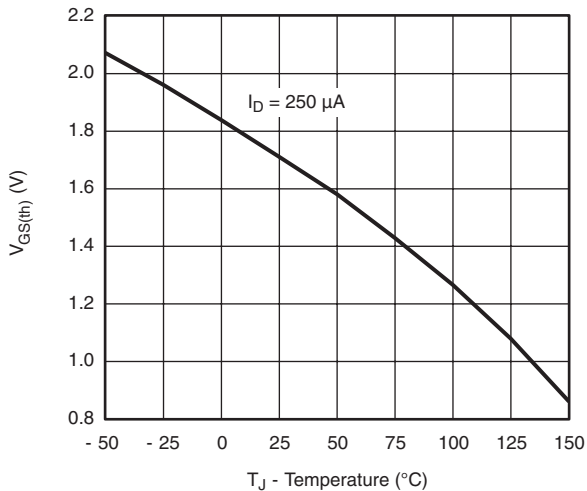
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



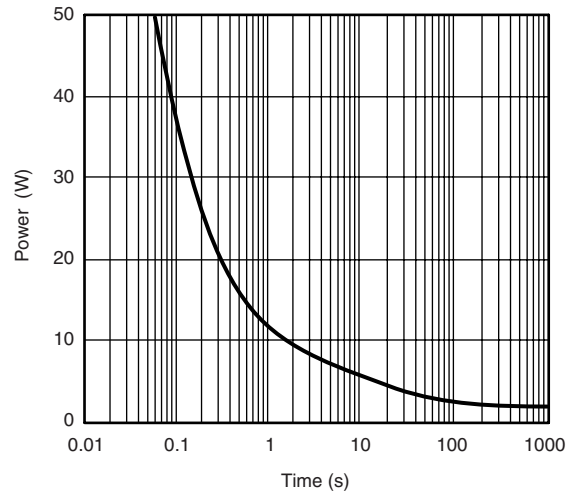
Source-Drain Diode Forward Voltage



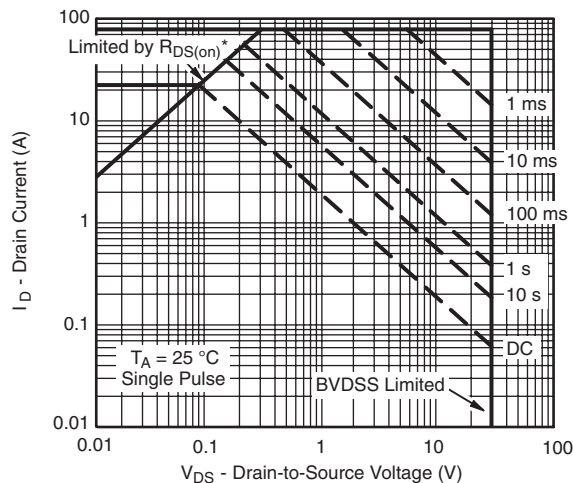
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



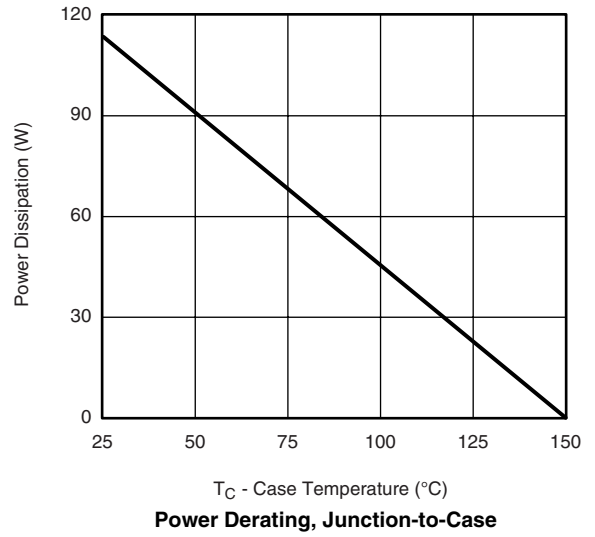
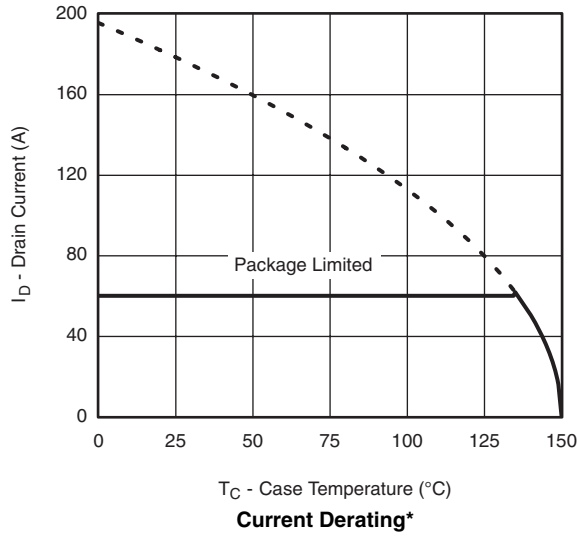
Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



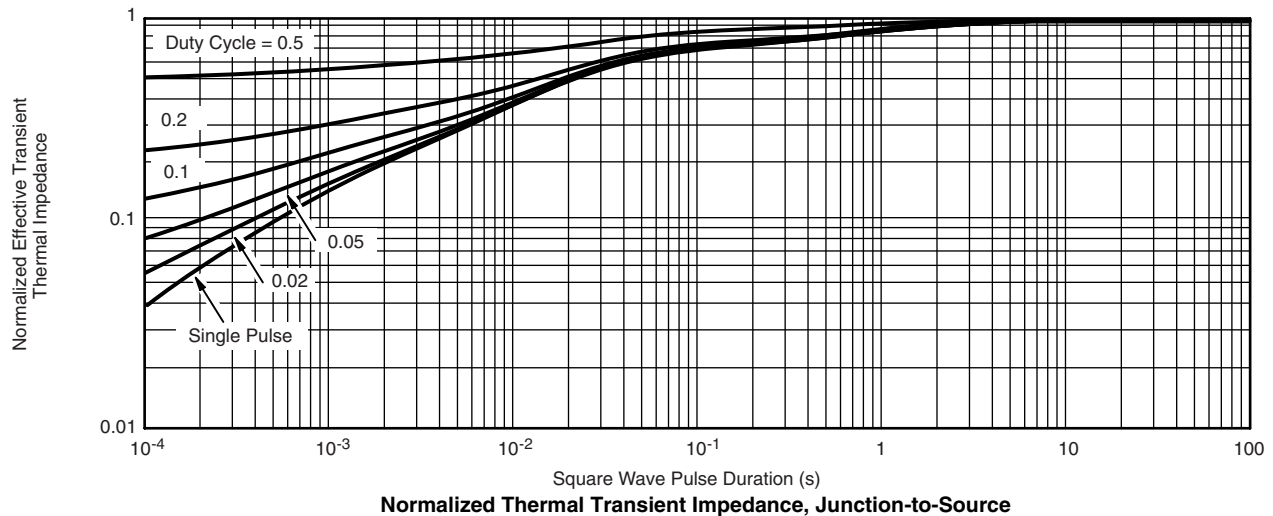
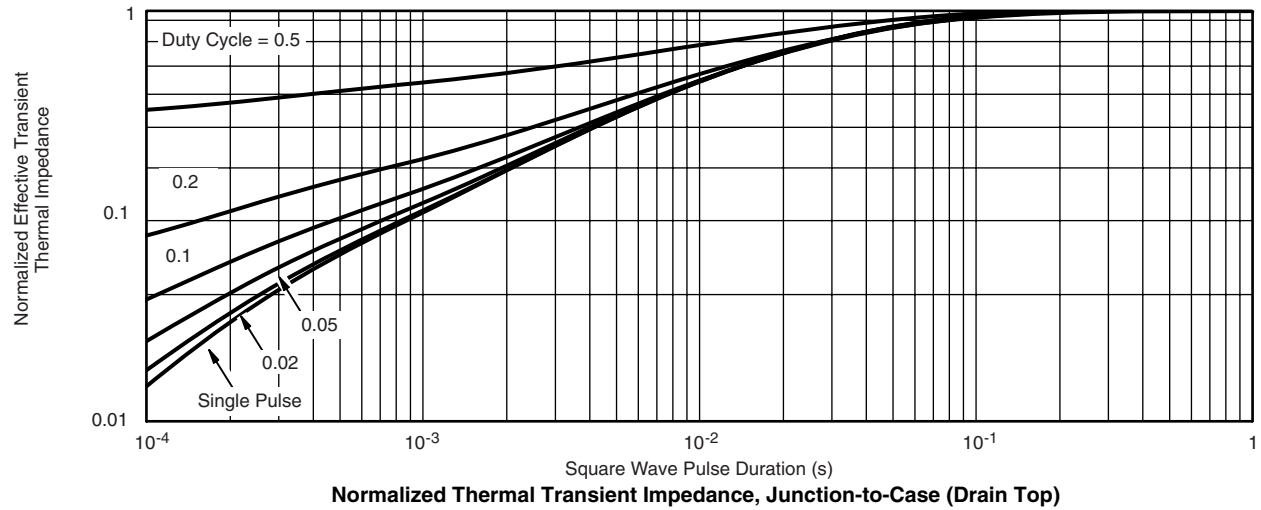
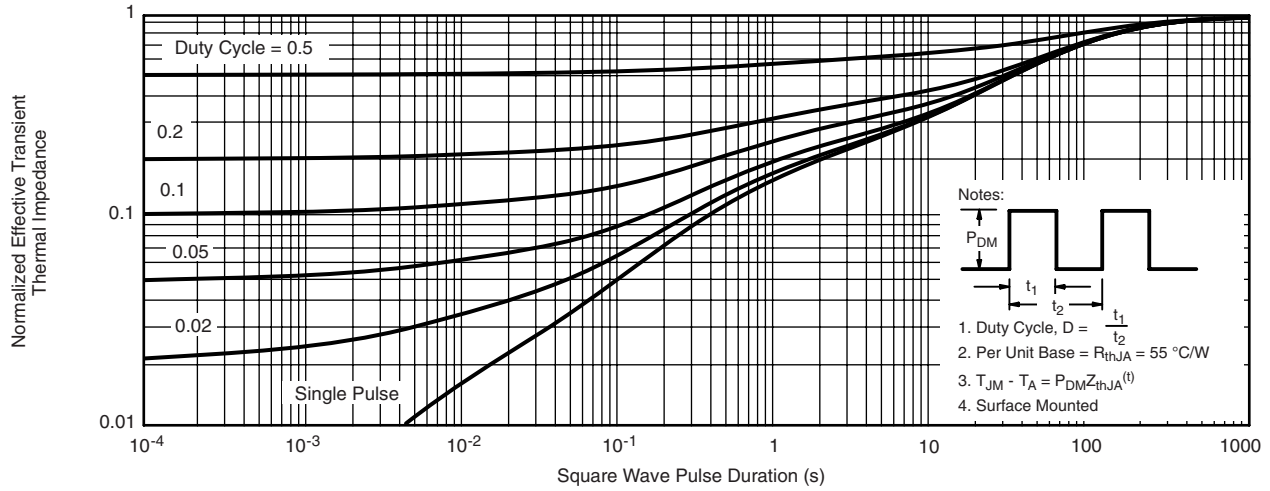
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SiE860DF



Vishay Siliconix 供应商

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68786.

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.